

# Alexey Novikov

## List of Publications by Citations

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23  
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189  
ext. papers

1,230  
ext. citations

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avg, IF

3.89  
L-index

#	Paper	IF	Citations
172	Quantum Dot Emission Driven by Mie Resonances in Silicon Nanostructures. <i>Nano Letters</i> , <b>2017</b> , 17, 6886-6892	3.4	81
171	Microscopic and optical investigation of Ge nanoislands on silicon substrates. <i>Nanotechnology</i> , <b>2002</b> , 13, 81-85	3.4	40
170	Observation of the electron-hole liquid in Si <sub>1-x</sub> Ge <sub>x</sub> /Si quantum wells by steady-state and time-resolved photoluminescence measurements. <i>Physical Review B</i> , <b>2010</b> , 82,	3.3	35
169	Growth and photoluminescence of self-assembled islands obtained during the deposition of Ge on a strained SiGe layer. <i>Optical Materials</i> , <b>2005</b> , 27, 818-821	3.3	31
168	Self-organization of germanium nanoislands obtained in silicon by molecular-beam epitaxy. <i>JETP Letters</i> , <b>1998</b> , 67, 48-53	1.2	27
167	SiGe nanostructures with self-assembled islands for Si-based optoelectronics. <i>Semiconductor Science and Technology</i> , <b>2011</b> , 26, 014029	1.8	25
166	Condensation of excitons and the spectrum of multiparticle states in SiGe/Si quantum wells: The role of the barrier in the conduction band. <i>JETP Letters</i> , <b>2011</b> , 94, 63-67	1.2	23
165	Antimony segregation in Ge and formation of n-type selectively doped Ge films in molecular beam epitaxy. <i>Journal of Applied Physics</i> , <b>2015</b> , 118, 145701	2.5	19
164	Monolithically integrated InGaAs/GaAs/AlGaAs quantum well laser grown by MOCVD on exact Ge/Si(001) substrate. <i>Applied Physics Letters</i> , <b>2016</b> , 109, 061111	3.4	19
163	Impact of growth and annealing conditions on the parameters of Ge/Si(001) relaxed layers grown by molecular beam epitaxy. <i>Semiconductors</i> , <b>2015</b> , 49, 1415-1420	0.7	18
162	Optical monitoring of technological parameters during molecular-beam epitaxy. <i>Semiconductors</i> , <b>2012</b> , 46, 1471-1475	0.7	18
161	Low-energy photoluminescence of structures with GeSi/Si(001) self-assembled nanoislands. <i>JETP Letters</i> , <b>2002</b> , 76, 365-369	1.2	18
160	Raman spectroscopy and electroreflectance studies of self-assembled SiGe nanoislands grown at various temperatures. <i>Physics of the Solid State</i> , <b>2005</b> , 47, 54	0.8	18
159	Usage of antimony segregation for selective doping of Si in molecular beam epitaxy. <i>Journal of Applied Physics</i> , <b>2011</b> , 109, 113533	2.5	17
158	Electron-hole liquid and excitonic molecules in quasi-two-dimensional SiGe layers of Si/SiGe/Si heterostructures. <i>JETP Letters</i> , <b>2010</b> , 92, 305-309	1.2	17
157	Gigantic uphill diffusion during self-assembled growth of Ge quantum dots on strained SiGe sublayers. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 141909	3.4	16
156	Strain-driven alloying: effect on sizes, shape and photoluminescence of GeSi/Si(001) self-assembled islands. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2002</b> , 89, 62-65	2.1	16

155	Towards the indium nitride laser: obtaining infrared stimulated emission from planar monocrystalline InN structures. <i>Scientific Reports</i> , <b>2018</b> , 8, 9454	4.9	15
154	Dynamics of the phase transitions in the system of nonequilibrium charge carriers in quantum-dimensional Si <sub>1-x</sub> Ge <sub>x</sub> /Si structures. <i>Journal of Experimental and Theoretical Physics</i> , <b>2013</b> , 117, 912-925	1	14
153	Channels of radiative recombination and phase transitions in a system of nonequilibrium carriers in a Si <sub>0.93</sub> Ge <sub>0.07</sub> /Si thin quantum well. <i>Journal of Experimental and Theoretical Physics</i> , <b>2008</b> , 107, 846-853 <sup>1</sup>		14
152	Photoluminescence of Ge(Si) self-assembled islands embedded in a tensile-strained Si layer. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 011914	3.4	14
151	Theoretical and experimental investigations of single- and multilayer structures with SiGe nanoislands. <i>Materials Science and Engineering C</i> , <b>2003</b> , 23, 1027-1031	8.3	14
150	The effect of local atomic structure on the optical properties of GeSi self-assembled islands buried in silicon matrix. <i>Nanotechnology</i> , <b>2007</b> , 18, 115711	3.4	13
149	The elastic strain and composition of self-assembled GeSi islands on Si(001). <i>Thin Solid Films</i> , <b>2000</b> , 367, 171-175	2.2	13
148	Electrically pumped InGaAs/GaAs quantum well microdisk lasers directly grown on Si(100) with Ge/GaAs buffer. <i>Optics Express</i> , <b>2017</b> , 25, 16754-16760	3.3	12
147	Features of two-dimensional to three-dimensional growth mode transition of Ge in SiGe/Si(001) heterostructures with strained layers. <i>Applied Physics Letters</i> , <b>2009</b> , 95, 151902	3.4	12
146	Effect of irradiation on the luminescence properties of low-dimensional SiGe/Si(001) heterostructures. <i>Semiconductors</i> , <b>2010</b> , 44, 329-334	0.7	12
145	Phonons in Ge/Si quantum dot structures: influence of growth temperature. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2004</b> , 21, 464-468	3	12
144	Light emission from Ge(Si)/SOI self-assembled nanoislands embedded in photonic crystal slabs of various periods with and without cavities. <i>Semiconductor Science and Technology</i> , <b>2019</b> , 34, 024003	1.8	12
143	Transition from dome to pyramid shape of self-assembled GeSi islands. <i>Journal of Crystal Growth</i> , <b>2000</b> , 209, 302-305	1.6	11
142	Photoluminescence line width of self-assembled Ge(Si) islands arranged between strained Si layers. <i>Semiconductors</i> , <b>2011</b> , 45, 198-202	0.7	10
141	Effect of parameters of Ge(Si)/Si(001) self-assembled islands on their electroluminescence at room temperature. <i>Semiconductors</i> , <b>2009</b> , 43, 313-317	0.7	10
140	Photoluminescence of dome and hut shaped Ge(Si) self-assembled islands embedded in a tensile-strained Si layer. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 021916	3.4	10
139	Cooperative effects in SiGe/Si quantum wells. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2008</b> , 40, 1172-1174	3	10
138	Comparative analysis of photoluminescence and electroluminescence of multilayer structures with self-assembled Ge(Si)/Si(001) island. <i>Semiconductors</i> , <b>2008</b> , 42, 286-290	0.7	10

137	Structural and electrical properties of Ge-on-Si(0 0 1) layers with ultra heavy n-type doping grown by MBE. <i>Journal of Crystal Growth</i> , <b>2018</b> , 491, 26-30	1.6	9
136	Fine structure of the emission spectrum of a two-dimensional electronhole liquid in SiGe/Si quantum wells. <i>JETP Letters</i> , <b>2016</b> , 104, 163-168	1.2	9
135	MOCVD Growth of InGaAs/GaAs/AlGaAs Laser Structures with Quantum Wells on Ge/Si Substrates. <i>Crystals</i> , <b>2018</b> , 8, 311	2.3	9
134	Multiparticle states and the factors that complicate an experimental observation of the quantum coherence in the exciton gas of SiGe/Si quantum wells. <i>Journal of Experimental and Theoretical Physics</i> , <b>2015</b> , 121, 1052-1066	1	9
133	TOF-SIMS 5 instrument sensitivity to matrix elements in GeSi Layers: Analysis based on recording of complex secondary ions. <i>Journal of Surface Investigation</i> , <b>2011</b> , 5, 591-594	0.5	9
132	Comparative analysis of radiation effects on the electroluminescence of Si and SiGe/Si(001) heterostructures with self-assembled Islands. <i>Semiconductors</i> , <b>2011</b> , 45, 225-229	0.7	9
131	Effects of boron and phosphorus doping on the photoluminescence of self-assembled germanium quantum dots. <i>Applied Physics Letters</i> , <b>2009</b> , 94, 183103	3.4	9
130	Electroluminescence and photoconductivity of GeSi heterostructures with self-assembled islands in the wavelength range 1.3-1.55 $\mu$ m. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2009</b> , 41, 935-938	3	9
129	Secondary cluster ions Ge <sup>+</sup> and Ge <sup>2+</sup> for improving depth resolution of SIMS depth profiling of GeSi/Si heterostructures. <i>Semiconductors</i> , <b>2010</b> , 44, 401-404	0.7	9
128	Formation of black silicon using SiGe self-assembled islands as a mask for selective anisotropic etching of silicon. <i>Materials Science in Semiconductor Processing</i> , <b>2018</b> , 75, 143-148	4.3	9
127	Impact of size distributions of Ge islands as etching masks for anisotropic etching on formation of anti-reflection structures. <i>Japanese Journal of Applied Physics</i> , <b>2019</b> , 58, 045505	1.4	8
126	Sb mediated formation of Ge/Si quantum dots: Growth and properties. <i>Thin Solid Films</i> , <b>2012</b> , 520, 3322-3325	8	
125	Real-time measurement of substrate temperature in molecular beam epitaxy using low-coherence tandem interferometry. <i>Journal of Crystal Growth</i> , <b>2015</b> , 413, 42-45	1.6	8
124	Intense photoluminescence from Ge(Si) self-assembled islands embedded in a tensile-strained Si layer. <i>Semiconductor Science and Technology</i> , <b>2007</b> , 22, S29-S32	1.8	8
123	Photoluminescence of self-assembled GeSi/Si(001) nanoislands of different shapes. <i>Physics of the Solid State</i> , <b>2004</b> , 46, 60-63	0.8	8
122	Influence of a predeposited Si <sub>1-x</sub> Gex layer on the growth of self-assembled SiGe/Si(001) islands. <i>Physics of the Solid State</i> , <b>2005</b> , 47, 26	0.8	8
121	Si <sub>1-x</sub> Gex/Si(001) relaxed buffer layers grown by chemical vapor deposition at atmospheric pressure. <i>Physics of the Solid State</i> , <b>2005</b> , 47, 42	0.8	8
120	Photonic Bound States in the Continuum in Si Structures with the Self-Assembled Ge Nanoislands. <i>Laser and Photonics Reviews</i> , <b>2021</b> , 15, 2000242	8.3	8

119	A new approach to the diagnostics of nanoislands in Ge x Si1 $\bar{k}$ /Si heterostructures by secondary ion mass spectrometry. <i>Technical Physics Letters</i> , <b>2014</b> , 40, 601-605	0.7	7
118	Selective etching of Si, SiGe, Ge and its usage for increasing the efficiency of silicon solar cells. <i>Semiconductors</i> , <b>2017</b> , 51, 1542-1546	0.7	7
117	Segregation of Sb in SiGe heterostructures grown by molecular beam epitaxy: Interdependence of growth conditions and structure parameters. <i>Journal of Crystal Growth</i> , <b>2014</b> , 396, 66-70	1.6	7
116	Radiation hardness of GeSi heterostructures with thin Ge layers. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2008</b> , 147, 191-194	3.1	7
115	Photoluminescence of Ge(Si)/Si(0 0 1) self-assembled islands in the near infra-red wavelength range. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2003</b> , 16, 467-472	3	7
114	Excitonic luminescence of SiGe/Si quantum wells doped with boron. <i>Journal of Applied Physics</i> , <b>2015</b> , 117, 185705	2.5	6
113	Barrier-height modification in Schottky silicon diodes with highly doped 3D and 2D layers. <i>Semiconductors</i> , <b>2012</b> , 46, 1358-1361	0.7	6
112	Influence of elastic strains in sublayers on the critical thickness of the Stranski-Krastanow transition for the GeSi/Si(001) system. <i>Journal of Surface Investigation</i> , <b>2009</b> , 3, 548-553	0.5	6
111	Distribution of germanium in Si1 $\bar{k}$ Ge x (x $\bar{k}$ ) Journal of Experimental and Theoretical Physics, <b>2009</b> , 109, 997-1010	1	6
110	Photoluminescence of GeSi/Si(0 0 1) self-assembled islands with dome and hut shape. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2004</b> , 23, 416-420	3	6
109	Influence of thermal annealing on the electrical and luminescent properties of heavily Sb-doped Ge/Si(001) layers. <i>Semiconductor Science and Technology</i> , <b>2018</b> , 33, 124019	1.8	6
108	On the stimulated emission of InGaAs/GaAs/AlGaAs laser structures grown by MOCVD on exact and inclined Ge/Si(001) substrates. <i>Semiconductors</i> , <b>2017</b> , 51, 663-666	0.7	5
107	Study of the Structural and Emission Properties of Ge(Si) Quantum Dots Ordered on the Si(001) Surface. <i>Semiconductors</i> , <b>2018</b> , 52, 1150-1155	0.7	5
106	Quantitative calibration and germanium SIMS depth profiling in Ge x Si1 $\bar{k}$ /Si heterostructures. <i>Semiconductors</i> , <b>2014</b> , 48, 1109-1117	0.7	5
105	Time-resolved photoluminescence from self-assembled Ge(Si) islands in multilayer SiGe/Si and SiGe/SOI structures. <i>Semiconductors</i> , <b>2013</b> , 47, 1496-1499	0.7	5
104	Peculiarities of growing InGaAs/GaAs/AlGaAs laser structures by MOCVD on Ge/Si substrates. <i>Semiconductors</i> , <b>2017</b> , 51, 1527-1530	0.7	5
103	Method for taking into account the shift parameter in the deconvolution of the depth composition distribution of semiconductor structures from SIMS depth profiles. <i>Semiconductors</i> , <b>2012</b> , 46, 1481-1486	0.7	5
102	Transition from planar to island growth mode in SiGe structures fabricated on SiGe/Si(001) strain-relaxed buffers. <i>Applied Physics Letters</i> , <b>2012</b> , 101, 151601	3.4	5

101	Special features of the formation of Ge(Si) islands on the relaxed Si <sub>1-x</sub> Ge <sub>x</sub> /Si(001) buffer layers. <i>Semiconductors</i> , <b>2006</b> , 40, 229-233	0.7	5
100	Fabrication of Strain-Relaxed Si <sub>1-x</sub> Ge <sub>x</sub> /Si(001) Buffer Layers of Low Surface Roughness. <i>Russian Microelectronics</i> , <b>2005</b> , 34, 203-209	0.5	5
99	Quantitative depth profiling of Si <sub>1-x</sub> Ge <sub>x</sub> structures by time-of-flight secondary ion mass spectrometry and secondary neutral mass spectrometry. <i>Thin Solid Films</i> , <b>2016</b> , 607, 25-31	2.2	5
98	Ordered Arrays of Ge(Si) Quantum Dots Incorporated into Two-Dimensional Photonic Crystals. <i>Semiconductors</i> , <b>2019</b> , 53, 1329-1333	0.7	4
97	Technology of the production of laser diodes based on GaAs/InGaAs/AlGaAs structures grown on a Ge/Si substrate. <i>Semiconductors</i> , <b>2017</b> , 51, 1477-1480	0.7	4
96	Control of surface dip diameter in Si-based photonic nanostructures by changing growth temperature of Ge quantum dot multilayer structures and its impact on their optical properties. <i>Japanese Journal of Applied Physics</i> , <b>2015</b> , 54, 08KA01	1.4	4
95	Excitation spectra of photoluminescence and its kinetics in structures with self-assembled Ge:Si nanoislands. <i>Semiconductors</i> , <b>2015</b> , 49, 1410-1414	0.7	4
94	Effect of silicon spacer thickness on the electroluminescence of multilayer structures with self-assembled Ge(Si)/Si(001) islands. <i>Semiconductors</i> , <b>2012</b> , 46, 1418-1422	0.7	4
93	Effects of the lateral ordering of self-assembled SiGe nanoislands grown on strained Si <sub>1-x</sub> Ge <sub>x</sub> buffer layers. <i>Semiconductors</i> , <b>2012</b> , 46, 647-654	0.7	4
92	Exciton condensation in the compressively strained SiGe layers of Si/SiGe/Si heterostructures. <i>Thin Solid Films</i> , <b>2008</b> , 517, 55-56	2.2	4
91	Influence of the germanium deposition rate on the growth and Photoluminescence of Ge(Si)/Si(001) self-assembled islands. <i>Physics of the Solid State</i> , <b>2005</b> , 47, 38	0.8	4
90	Ge self-assembled islands grown on SiGe/Si(001) relaxed buffer layers. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2005</b> , 124-125, 466-469	3.1	4
89	Shallow acceptors in Ge/GeSi multi-quantum well heterostructures. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2000</b> , 7, 608-611	3	4
88	Luminescence of Spatially Ordered Self-Assembled Solitary Ge(Si) Nanoislands and their Groups Incorporated into Photonic Crystals. <i>Semiconductors</i> , <b>2020</b> , 54, 853-859	0.7	4
87	Features of InN growth by nitrogen-plasma-assisted MBE at different ratios of fluxes of group-III and -V elements. <i>Semiconductors</i> , <b>2016</b> , 50, 261-265	0.7	4
86	Coupling of Germanium Quantum Dots with Collective Sub-radiant Modes of Silicon Nanopillar Arrays. <i>ACS Photonics</i> , <b>2021</b> , 8, 209-217	6.3	4
85	Impact of Ge deposition temperature on parameters of c-Si solar cells with surface texture formed by etching of Si using SiGe islands as a mask. <i>Materials Science in Semiconductor Processing</i> , <b>2020</b> , 114, 105065	4.3	3
84	Influence of Annealing on the Properties of Ge:Sb/Si(001) Layers with an Antimony Concentration Above Its Equilibrium Solubility in Germanium. <i>Semiconductors</i> , <b>2019</b> , 53, 882-886	0.7	3

83	Use of related parameters in X-ray diffraction analysis of multilayer structures with allowance for the layer growth time. <i>Technical Physics</i> , <b>2014</b> , 59, 402-406	0.5	3
82	Transition from the two- to three-dimensional growth of Ge films upon deposition onto relaxed SiGe/Si(001) buffer layers. <i>Semiconductors</i> , <b>2013</b> , 47, 427-432	0.7	3
81	Growth of light-emitting SiGe heterostructures on strained silicon-on-insulator substrates with a thin oxide layer. <i>Semiconductors</i> , <b>2015</b> , 49, 1104-1110	0.7	3
80	Effect of tensile-strained Si layer on photoluminescence of Ge(Si) self-assembled islands grown on relaxed SiGe/Si(001) buffer layers. <i>Semiconductors</i> , <b>2007</b> , 41, 167-171	0.7	3
79	Effect of growth temperature on photoluminescence of self-assembled Ge(Si) islands confined between strained Si layers. <i>Semiconductors</i> , <b>2007</b> , 41, 1356-1360	0.7	3
78	Comparative analysis of photo- and electroluminescence of multilayer structures with Ge(Si)/Si(001) self-assembled islands. <i>Thin Solid Films</i> , <b>2008</b> , 517, 398-400	2.2	3
77	Elastic strain and composition of self-assembled GeSi nanoislands on Si(001). <i>Semiconductors</i> , <b>2000</b> , 34, 6-10	0.7	3
76	Ultrasensitive Detection of Mercury Ions Under UV Illumination of MoS <sub>2</sub> Functionalized AlGa <sub>N</sub> /Ga <sub>N</sub> Transistor. <i>IEEE Transactions on Electron Devices</i> , <b>2020</b> , 67, 5693-5700	2.9	3
75	One-Stage Formation of Two-Dimensional Photonic Crystal and Spatially Ordered Arrays of Self-Assembled Ge(Si) Nanoislandson Pit-Patterned Silicon-On-Insulator Substrate. <i>Nanomaterials</i> , <b>2021</b> , 11,	5.4	3
74	Fabrication of light-trapping structure by selective etching of thin Si substrates masked with a Ge dot layer and nanomasks. <i>Japanese Journal of Applied Physics</i> , <b>2018</b> , 57, 08RF09	1.4	3
73	On the Application of Strain-Compensating GaAsP Layers for the Growth of InGaAs/GaAs Quantum-Well Laser Heterostructures Emitting at Wavelengths above 1100 nm on Artificial Ge/Si Substrates. <i>Semiconductors</i> , <b>2018</b> , 52, 1547-1550	0.7	3
72	Spin pump induced inverse spin Hall effect observed in Bi-doped n-type Si. <i>Physical Review B</i> , <b>2020</b> , 101,	3.3	2
71	Plasmonic enhancement of four-particle radiative recombination in SiGe quantum wells. <i>JETP Letters</i> , <b>2016</b> , 104, 231-235	1.2	2
70	Formation of light-trapping structure using Ge islands grown by gas-source molecular beam epitaxy as etching masks. <i>Japanese Journal of Applied Physics</i> , <b>2018</b> , 57, 08RB04	1.4	2
69	Emission Properties of Heavily Doped Epitaxial Indium-Nitride Layers. <i>Semiconductors</i> , <b>2019</b> , 53, 1357-1362	0.7	2
68	The waveguide effect of InGaAs quantum wells in a GaAs structure on Si substrate with Ge buffer layer. <i>Technical Physics Letters</i> , <b>2015</b> , 41, 648-650	0.7	2
67	New approach to the X-ray diffraction analysis of test structures during flow calibration in epitaxial growth reactors. <i>Journal of Surface Investigation</i> , <b>2012</b> , 6, 494-497	0.5	2
66	Segregation of Sb in Ge epitaxial layers and its usage for the selective doping of Ge-based structures. <i>Semiconductors</i> , <b>2015</b> , 49, 1405-1409	0.7	2

65	Layer-by-layer analysis of structures containing $\delta$ layers by secondary ion mass spectrometry taking into account the TOF.SIMS-5 depth resolution function. <i>Journal of Surface Investigation</i> , <b>2012</b> , 6, 574-577 <sup>0.5</sup>	2
64	Photoluminescence excitation spectroscopy technique modified for studying structures with self-assembled Ge(Si)/Si(001) nanoislands. <i>Technical Physics Letters</i> , <b>2012</b> , 38, 828-831	0.7 2
63	Direct comparison of superlattice periods measured with X-ray diffractometry and optical interferometry. <i>Bulletin of the Russian Academy of Sciences: Physics</i> , <b>2011</b> , 75, 40-43	0.4 2
62	Study of the transition of the epitaxial Ge film from layer-to-layer to three-dimensional growth in heterostructures with strained SiGe sublayers. <i>Semiconductors</i> , <b>2010</b> , 44, 519-524	0.7 2
61	Impurity photoconductivity in SiGe/Si:B multi-quantum-well heterostructures. <i>Physica B: Condensed Matter</i> , <b>2003</b> , 340-342, 1065-1068	2.8 2
60	Atomic-force-microscopy visualization of GeSi buried nanoislands on crystal cleavages in silicon structures. <i>Semiconductors</i> , <b>2003</b> , 37, 667-674	0.7 2
59	Experimental and theoretical study of the influence of growth temperature on composition in self-assembled SiGe QD's. <i>Materials Science and Engineering C</i> , <b>2005</b> , 25, 565-569	8.3 2
58	GeSi/Si(001) Structures with Self-Assembled Islands: Growth and Optical Properties <b>2005</b> , 333-351	2
57	Magnetotransport in Si langleSb rangle Delta-Layer after Swift Heavy Ion-Induced Modification. <i>Acta Physica Polonica A</i> , <b>2017</b> , 132, 229-232	0.6 2
56	Nonlinear calibration curves in secondary ion mass spectrometry for quantitative analysis of gesi heterostructures with nanoclusters. <i>Technical Physics Letters</i> , <b>2016</b> , 42, 243-247	0.7 2
55	Formation and Properties of Locally Tensile Strained Ge Microstructures for Silicon Photonics. <i>Semiconductors</i> , <b>2018</b> , 52, 1442-1447	0.7 2
54	Mercury (II) Ion Detection using AgNWs-MoS2 Nanocomposite on GaN HEMT for IoT Enabled Smart Water Quality Analysis. <i>IEEE Internet of Things Journal</i> , <b>2021</b> , 1-1	10.7 2
53	Heating and evaporation of a two-dimensional electronhole liquid by heat pulses. <i>JETP Letters</i> , <b>2017</b> , 105, 179-184	1.2 1
52	Comparative Analysis of the Luminescence of Ge:Sb Layers Grown on Ge(001) and Si(001) Substrates. <i>Semiconductors</i> , <b>2019</b> , 53, 1318-1323	0.7 1
51	Locally Strained Ge/SOI Structures with an Improved Heat Sink as an Active Medium for Silicon Optoelectronics. <i>Semiconductors</i> , <b>2019</b> , 53, 1324-1328	0.7 1
50	Antimony segregation in stressed SiGe heterostructures grown by molecular beam epitaxy. <i>Semiconductors</i> , <b>2013</b> , 47, 1481-1484	0.7 1
49	Investigation of deformations and strain fields in silicon matrix structures embedded with vertically stacked Ge(Si) self-assembled islands. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 161910	3.4 1
48	Method of selective doping of silicon by segregating impurities. <i>Technical Physics Letters</i> , <b>2011</b> , 37, 824-826	1



47	Composition and elastic stresses in multilayer structures with Si <sub>1-x</sub> Ge <sub>x</sub> nanoislands. <i>Physics of the Solid State</i> , <b>2004</b> , 46, 85-88	0.8	1
46	Visualization of buried SiGe quantum dots at cleavages by cross-sectional atomic force microscopy. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 1999-2001	3.4	1
45	Negative photoconductivity of selectively doped SiGe/Si: B heterostructures with a two-dimensional hole gas in the middle-infrared range. <i>Physics of the Solid State</i> , <b>2005</b> , 47, 46	0.8	1
44	Near-infrared stimulated emission from indium-rich InGaN layers grown by plasma-assisted MBE. <i>Applied Physics Letters</i> , <b>2021</b> , 118, 151902	3.4	1
43	Influence of surface roughness on a change in the growth mode from two-dimensional to three-dimensional for strained SiGe heterostructures. <i>Semiconductors</i> , <b>2016</b> , 50, 1630-1634	0.7	1
42	Features of SOI substrates heating in MBE growth process obtained by low-coherence tandem interferometry. <i>Journal of Crystal Growth</i> , <b>2016</b> , 448, 89-92	1.6	1
41	Pulsed Ion-Beam Treatment of Germanium Implanted by Antimony Ions. <i>Optoelectronics, Instrumentation and Data Processing</i> , <b>2019</b> , 55, 423-430	0.6	1
40	A New Limitation of the Depth Resolution in TOF-SIMS Elemental Profiling: the Influence of a Probing Ion Beam. <i>Technical Physics Letters</i> , <b>2018</b> , 44, 320-323	0.7	1
39	Luminescent properties of spatially ordered Ge/Si quantum dots epitaxially grown on a pit-patterned silicon-on-insulator substrate. <i>Journal of Luminescence</i> , <b>2022</b> , 249, 119033	3.8	1
38	Influence of the Growth Conditions and Doping Level on the Luminescence Kinetics of Ge:Sb Layers Grown on Silicon. <i>Semiconductors</i> , <b>2020</b> , 54, 811-816	0.7	0
37	Effect of antimony doping on the energy of optical transitions in n-Ge layers grown on Si (001) and Ge (001) substrates. <i>Journal of Applied Physics</i> , <b>2020</b> , 127, 165701	2.5	0
36	Epitaxial GaN layers formed on langasite substrates by the plasma-assisted MBE method. <i>Semiconductors</i> , <b>2016</b> , 50, 1511-1514	0.7	0
35			
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| 6  | $\text{GaAs}/\text{InGaAs}/\text{AlGaAs}$ , $\text{Ge}/\text{Si}$ <i>Fizika I Tekhnika Poluprovodnikov</i> , <b>2017</b> , 51, 1530  | 0   |
| 5  | $\text{InGaAs}/\text{GaAs}/\text{AlGaAs}$ $\text{Ge}/\text{Si}$ . <i>Fizika I Tekhnika Poluprovodnikov</i> , <b>2017</b> , 51, 1579  | 0   |
| 4  | Comparative analysis of photoluminescence and electroluminescence of multilayer structures with self-assembled Ge(Si)/Si(001) island <b>2010</b> , 42, 286   |     |
| 3  | Visible Emission from a Dense Biexciton Gas in SiGe/Si Quantum Wells under External Anisotropic Strain. <i>JETP Letters</i> , <b>2018</b> , 107, 358-363   | 1.2 |
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| 1  | Stimulated Emission at 1.3- $\mu\text{m}$ Wavelength in Metamorphic InGaAs/InGaAsP Structure with Quantum Wells Grown on Ge/Si(001) Substrate. <i>Technical Physics Letters</i> , <b>2018</b> , 44, 735-738            | 0.7 |